

# Supporting Information

## Air Stable $p$ -Doping of $\text{WSe}_2$ by Covalent Functionalization

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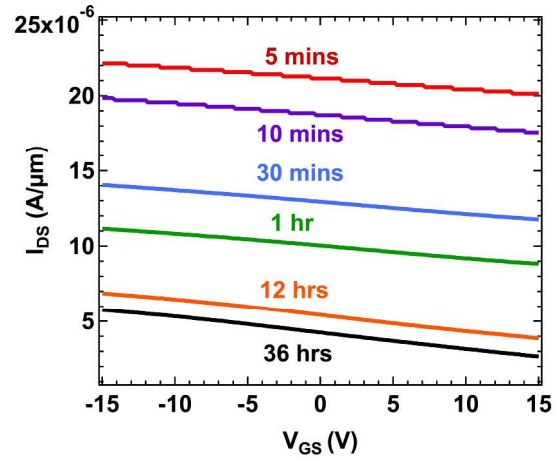
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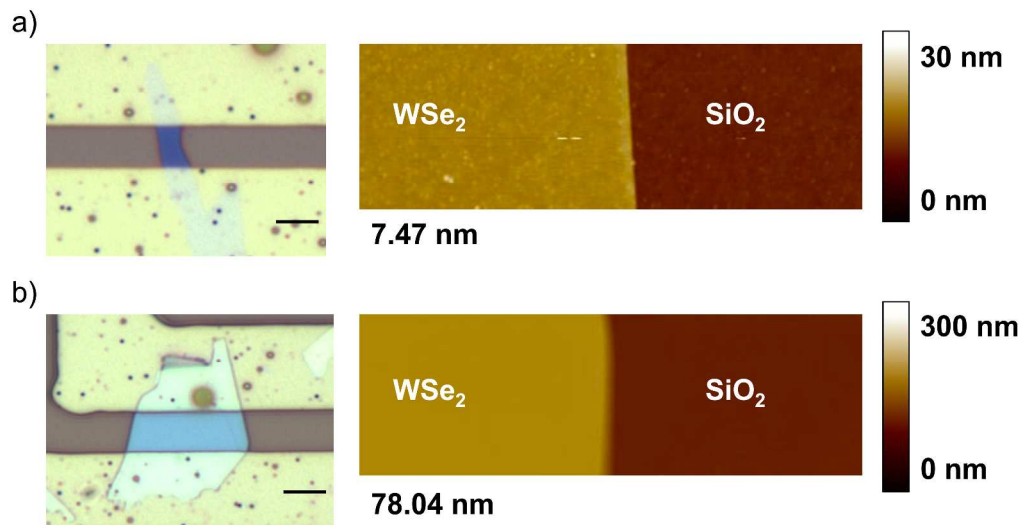
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**Figure S1.** Facsimile of Figure 1(d) represented in linear scale for drain current. A degenerate p-type trend is observed with small on/off ratio and slightly lower drain current at a more positive gate bias.



**Figure S2.** Optical microscopy (left) and atomic force microscopy (AFM, right) images of devices shown in Figure 5. WSe<sub>2</sub> layer thicknesses are (a) ~7.5nm and (b) ~ 78 nm. Scale bar is 3μm.